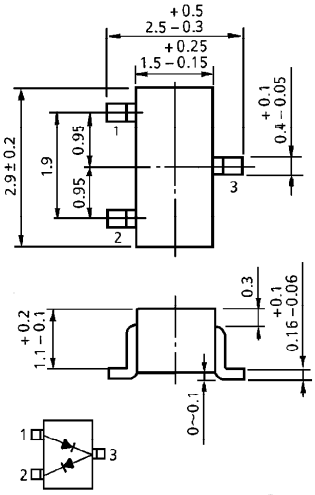
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS396

LOW VOLTAGE HIGH SPEED SWITCHING

Unit in mm

- Low Forward Voltage : $V_{F(3)}$ = 0.54V (Typ.)
- Low Reverse Current : I_R = 5μA (Max.)
- Small Package : SC-59



S-MINI	
JEDEC	TO-236MOD
EIAJ	SC-59
TOSHIBA	1-3G1G

Weight : 0.012g

MAXIMUM RATINGS (Ta = 25°C)

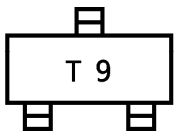
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Maximum (Peak) Forward Current	I_{FM}	300*	mA
Average Forward Current	I_O	100*	mA
Surge Current (10ms)	I_{FSM}	1*	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C
Operation Temperature Range	T_{opr}	−40~100	°C

* : Unit Rating. Total Rating = Unit Rating × 0.7

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F = 1mA	—	0.28	—	V
	$V_{F(2)}$	I_F = 10mA	—	0.36	—	
	$V_{F(3)}$	I_F = 100mA	—	0.54	0.60	
Reverse Current	I_R	V_R = 40V	—	—	5	μA
Total Capacitance	C_T	V_R = 0, f = 1MHz	—	18	25	pF

MARKING



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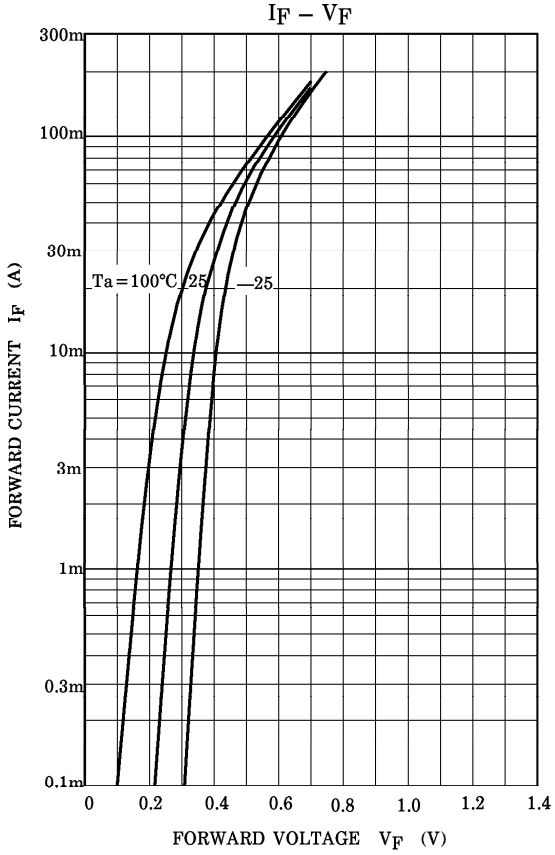
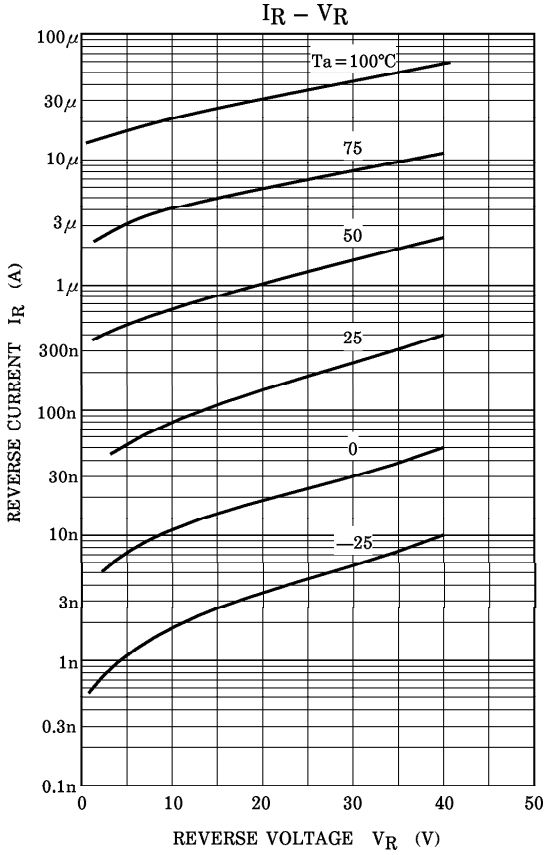
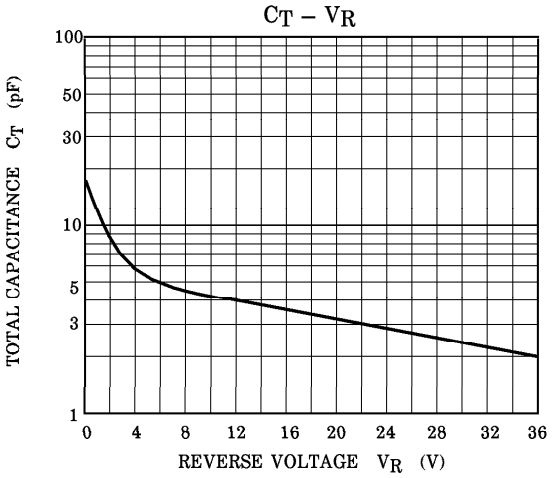
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



P – Ta